

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) A liquid crystal display device, comprising:
an active matrix substrate;
a counter substrate; and
a liquid crystal layer interposed between the active matrix substrate and the counter substrate, wherein the active matrix substrate includes:
a plate;
a thin film transistor provided on the plate; and
a side light shielding layer for covering at least a portion of a side surface of the thin film transistor and side surfaces of first, second and third interlayer insulating layers,
wherein the side light shielding layer is substantially vertically oriented,
wherein a top surface of a dummy insulating layer is substantially at the same level as a top surface of the third interlayer insulating layer with a fourth interlayer insulating layer provided between the dummy insulating layer and the side light shielding layer.

2. (Original) A liquid crystal display device according to claim 1, wherein the active matrix substrate further includes a semiconductor layer, and the thin film transistor includes a part of the semiconductor layer.

3. (Original) A liquid crystal display device according to claim 1, wherein:
the thin film transistor includes a gate electrode, a source electrode, and a drain electrode, and

the active matrix substrate further includes a pixel electrode, a gate line acting as the gate electrode of the thin film transistor, and a signal line connected to the source electrode of the thin film transistor.

4. (Original) A liquid crystal display device according to claim 2, wherein:
the active matrix substrate further includes an insulating layer provided on the plate and having a stepped portion having a side wall substantially perpendicular to the plate;
the semiconductor layer is provided on the stepped portion of the insulating layer;
and
the side light shielding layer is provided along the side wall of the stepped portion of the insulating layer.

5. (Original) A liquid crystal display device according to claim 1, wherein the active matrix substrate further includes a lower light shielding layer provided below the thin film transistor.

6. (Original) A liquid crystal display device according to claim 5, wherein the side light shielding layer is in contact with the lower light shielding layer.

7. (Original) A liquid crystal display device according to claim 1, wherein the active matrix substrate further includes an upper light shielding layer provided on the thin film transistor.

8. (Original) A liquid crystal display device according to claim 3, wherein the side light shielding layer is provided so as to cover a side surface of the gate line.

9. (Original) A liquid crystal display device according to claim 3, wherein the side light shielding layer is provided so as to cover a side surface of the signal line.

10. (Original) A liquid crystal display device according to claim 5, wherein the active matrix substrate further includes an additional capacitance electrode.

11. (Original) A liquid crystal display device according to claim 10, wherein the additional capacitance electrode is provided below the lower light shielding layer.

12. (Original) A liquid crystal display device according to claim 10, wherein the additional capacitance electrode is provided between the lower light shielding layer and the thin film transistor.

13. (Original) A liquid crystal display device according to claim 10, wherein the additional capacitance electrode is connected to the thin film transistor.

14. (Original) A liquid crystal display device according to claim 10, wherein the side light shielding layer is in contact with the additional capacitance electrode.

15. (Original) A liquid crystal display device according to claim 1, wherein the thin film transistor has an LDD structure.

16. (Original) A liquid crystal display device according to claim 1, wherein the side light shielding layer is formed of polycrystalline silicon.

17. (Original) A liquid crystal display device according to claim 1, wherein the side light shielding layer is formed of metal or metal silicide.

18. (Original) A liquid crystal display device according to claim 1,
wherein the side light shielding layer has a two-component structure including
metal or metal silicide and polycrystalline silicon.

19. (Currently amended) A method for producing a liquid crystal display device
including an active matrix substrate, a counter substrate, and a liquid crystal layer
interposed between the active matrix substrate and the counter substrate, the method
comprising:

forming a thin film transistor on a plate of the active matrix substrate; ~~and~~
forming a side light shielding layer for covering at least a portion of a side surface
of the thin film transistor and side surfaces of first, second and third interlayer insulating
layers, wherein the side light shielding layer is substantially vertically oriented, and
forming a top surface of a dummy insulating layer at substantially the same level
as a top surface of the third interlayer insulating layer with a fourth interlayer insulating
layer formed between the dummy insulating layer and the side light shielding layer .

20. (Original) A method according to claim 19, wherein the step of forming the
thin film transistor includes the step of forming a semiconductor layer used as a part of
the thin film transistor.

21. (Original) A method according to claim 20, further comprising the step of forming a first insulating layer on the plate, the first insulating layer having a stepped portion having a side wall substantially perpendicular to the plate, wherein:

the step of forming the semiconductor layer includes the step of forming the semiconductor layer on the stepped portion of the first insulating layer, and

the step of forming the side light shielding layer includes the step of forming the side light shielding layer along the side wall of the stepped portion of the first insulating layer.

22 (Original) A method according to claim 21, wherein the step of forming the side light shielding layer includes the steps of forming a layer of a material of the side light shielding layer so as to cover the stepped portion of the first insulating layer, and partially removing the layer by dry etching.

23. (Original) A method according to claim 21, further comprising the steps of forming a second insulating layer on the semiconductor layer, and flattening a surface of the second insulating layer before the stepped portion of the first insulating layer is formed.

24. (Original) A method according to claim 23, wherein the step of flattening the surface of the second insulating layer includes the step of flattening the second insulating layer by chemical mechanical polishing.

25. (Currently amended) A liquid crystal display device, comprising:
an active matrix substrate;
a counter substrate; and
a liquid crystal layer interposed between the active matrix substrate and the counter substrate, wherein the active matrix substrate includes:
a plate;
a thin film transistor provided on the plate; and
a side light shielding layer for covering at least a portion of a side surface of the thin film transistor, wherein in an area of the transistor the side light shielding layer is provided along and directly contacts sidewalls of first, second and third insulating films which are deposited in different steps;

wherein a top surface of a dummy insulating layer is substantially at the same level as a top surface of the third interlayer insulating film, with a fourth interlayer insulating film provided between the dummy insulating layer and the side light shielding film.

26. (Previously presented) The display device of claim 25, wherein the side light shielding layer is substantially vertically oriented.

27. (New) A liquid crystal display device, comprising:

- an active matrix substrate;
- a counter substrate; and
- a liquid crystal layer interposed between the active matrix substrate and the counter substrate, wherein the active matrix substrate includes:
 - a plate;
 - a thin film transistor provided on the plate, the thin film transistor comprising a gate, gate insulating film, source and drain;
 - an insulating film provided over the thin film transistor, said insulating film having at least one hole defined therein; and
 - a side light shielding layer for covering at least a portion of a side surface of the thin film transistor and being located on at least a sidewall of said hole in the insulating film, wherein the side light shielding layer is substantially vertically oriented, and wherein the side light shielding layer is located in said hole in the insulating film that is provided over the thin film transistor, and wherein no portion of the side light shielding film is located in any hole defined in an insulating film that is not formed over the thin film transistor.